

ABSTRACT OF THE DISCLOSURE

To enhance the emission output of the light emitting device including an active layer made of nitride semiconductor containing In, the light emitting device having an active layer between the n-type semiconductor layer and the p-type semiconductor layer, characterized in that the active layer comprises an well layer made of $\text{In}_{x1}\text{Ga}_{1-x1}\text{N}$ ($x1>0$) containing In and a first barrier layer made of $\text{Al}_{y2}\text{Ga}_{1-y2}\text{N}$ ($y2>0$) containing Al formed on the well layer.



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